

# LL4448PF

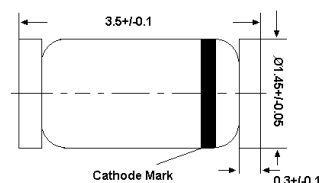
## Silicon Epitaxial Planar Switching Diode

Fast switching diode in MiniMELF case especially suited  
 For automatic surface mounting.  
 Identical electrically to standard 1N4448.

### Features

- Lead Free

LL-34



Glass case MiniMELF  
 Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	100	V
Reverse Voltage	$V_R$	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Surge Forward Current at $t < 1\text{ s}$	$I_{FSM}$	500	mA
Power Dissipation	$P_{tot}$	500 <sup>1)</sup>	mW
Junction Temperature	$T_j$	175	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 175	$^\circ\text{C}$

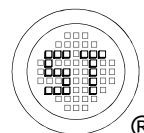
<sup>1)</sup> Valid provided that electrodes are kept at ambient temperature.

### Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	300	$^\circ\text{C/W}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 100\text{ mA}$	$V_F$	0.62 -	0.72 1	V
Reverse Leakage Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$	$I_R$ $I_R$ $I_R$	- - -	25 5 50	nA $\mu\text{A}$ $\mu\text{A}$
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	100	-	V
Capacitance at $V_R = 0$ , $f = 1\text{ MHz}$	$C_{tot}$	-	4	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ , $I_{rr} = 0.1 \times I_R$ , $V_R = 6\text{ V}$ , $R_L = 100\text{ }\Omega$	$t_{rr}$	-	4	ns



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## Electrical Characteristics Curves

Fig 1. Forward Characteristics

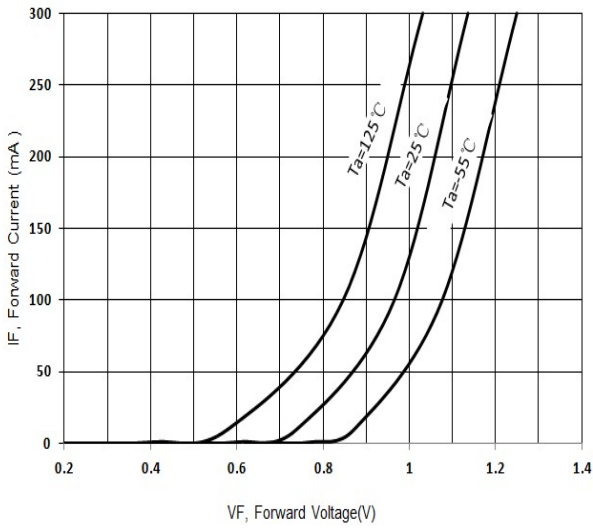


Fig 2. Reverse Characteristics

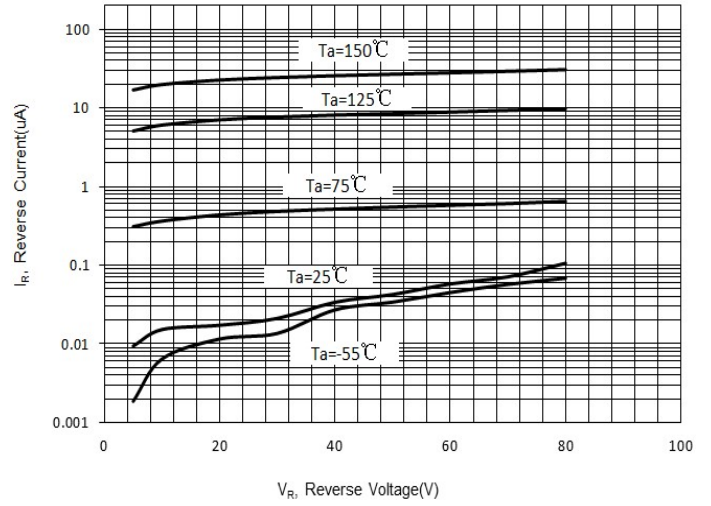


Fig 3. Junction Capacitance

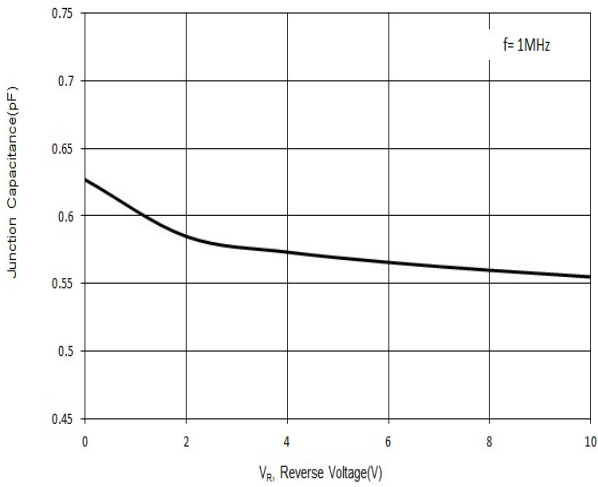


Fig 4. Power Derating Curves

